

MITSUBISHI Nch POWER MOSFET

FS30KMJ-3

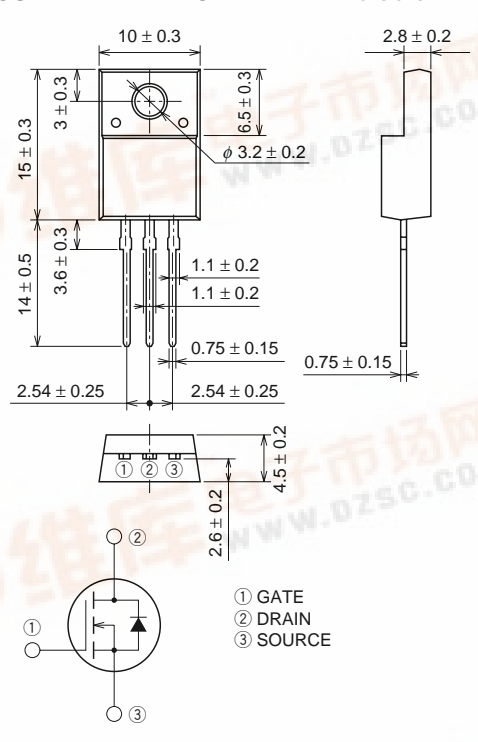
HIGH-SPEED SWITCHING USE

FS30KMJ-3



- 4V DRIVE
- V_{DSS} 150V
- $r_{DS(ON)}(MAX)$ 86m Ω
- I_D 30A
- Integrated Fast Recovery Diode (TYP.) 100ns
- V_{iso} 2000V

OUTLINE DRAWING Dimensions in mm



① GATE
② DRAIN
③ SOURCE

TO-220FN

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	$V_{GS} = 0V$	150	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		30	A
I_{DM}	Drain current (Pulsed)		120	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 100\mu H$	30	A
I_S	Source current		30	A
I_{SM}	Source current (Pulsed)		120	A
P_D	Maximum power dissipation		30	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
V_{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g



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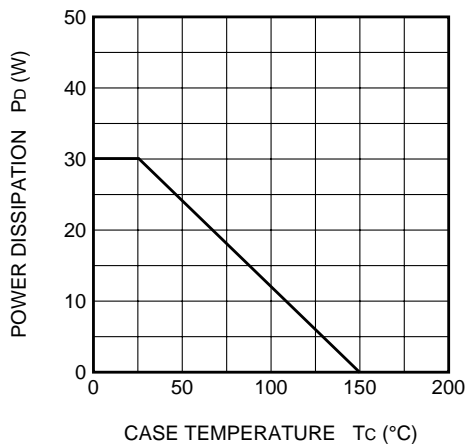
HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

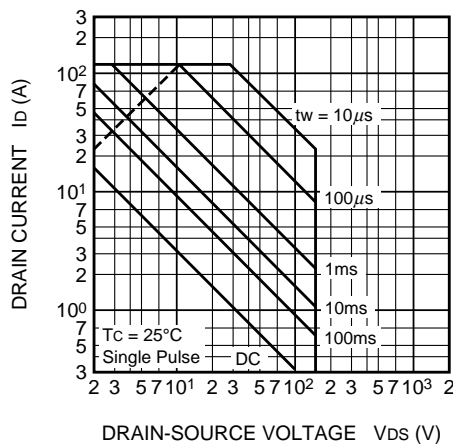
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	Id = 1mA, VGS = 0V	150	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = 150V, VGS = 0V	—	—	0.1	mA
VGS(th)	Gate-source threshold voltage	Id = 1mA, VDS = 10V	1.0	1.5	2.0	V
rDS(ON)	Drain-source on-state resistance	Id = 15A, VGS = 10V	—	66	86	mΩ
rDS(ON)	Drain-source on-state resistance	Id = 15A, VGS = 4V	—	69	90	mΩ
VDS(ON)	Drain-source on-state voltage	Id = 15A, VGS = 10V	—	0.99	1.29	V
yfs	Forward transfer admittance	Id = 15A, VDS = 10V	—	38	—	S
Ciss	Input capacitance	VDS = 10V, VGS = 0V, f = 1MHz	—	3000	—	pF
Coss	Output capacitance		—	320	—	pF
Crss	Reverse transfer capacitance		—	160	—	pF
td(on)	Turn-on delay time	VDD = 80V, Id = 15A, VGS = 10V, RGEN = RGS = 50Ω	—	22	—	ns
tr	Rise time		—	42	—	ns
td(off)	Turn-off delay time		—	280	—	ns
tf	Fall time		—	130	—	ns
VSD	Source-drain voltage	Is = 15A, VGS = 0V	—	1.0	1.5	V
Rth(ch-c)	Thermal resistance	Channel to case	—	—	4.17	°C/W
trr	Reverse recovery time	Is = 30A, dis/dt = -100A/μs	—	100	—	ns

PERFORMANCE CURVES

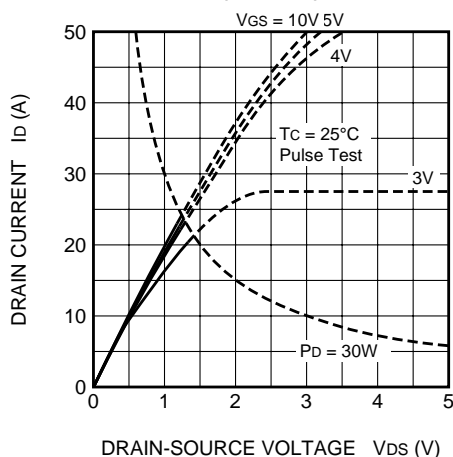
POWER DISSIPATION DERATING CURVE



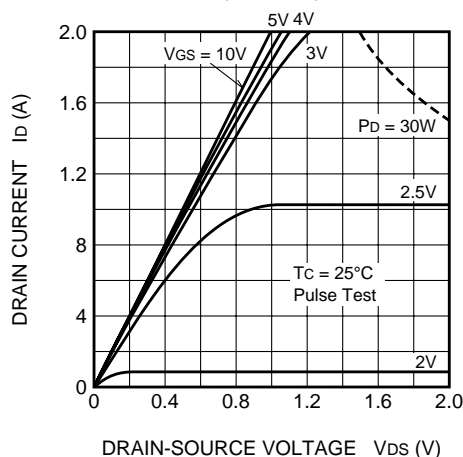
MAXIMUM SAFE OPERATING AREA



OUTPUT CHARACTERISTICS (TYPICAL)

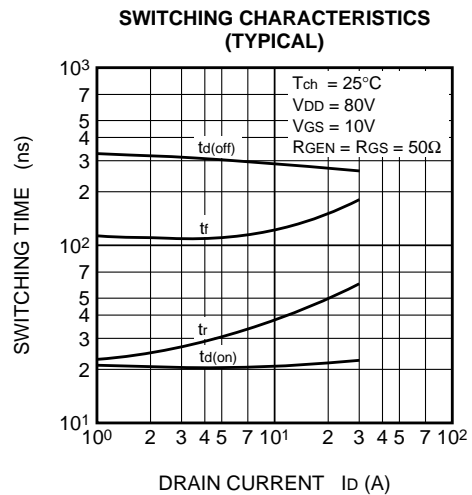
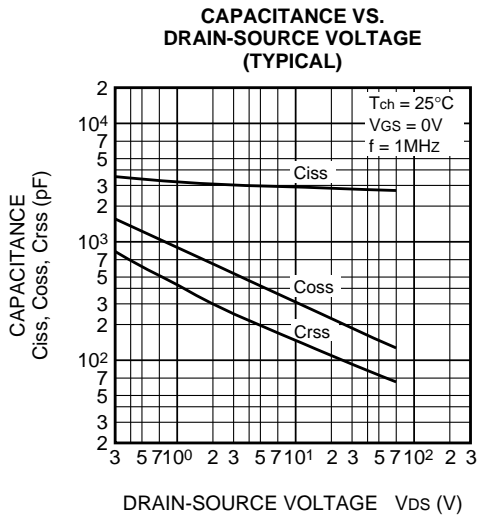
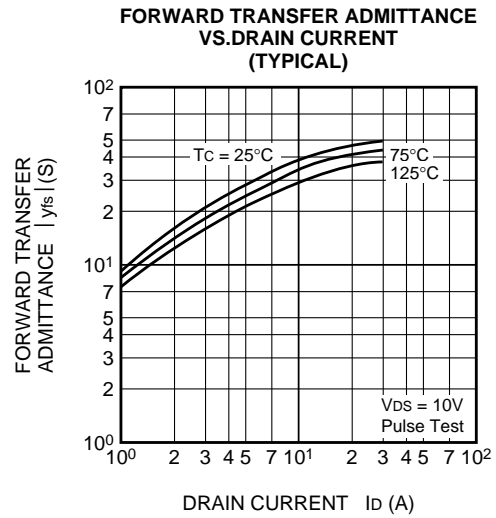
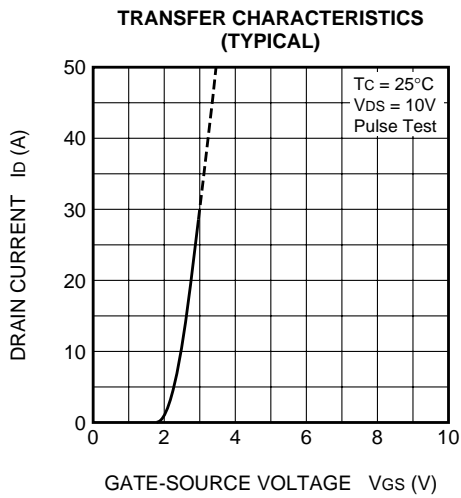
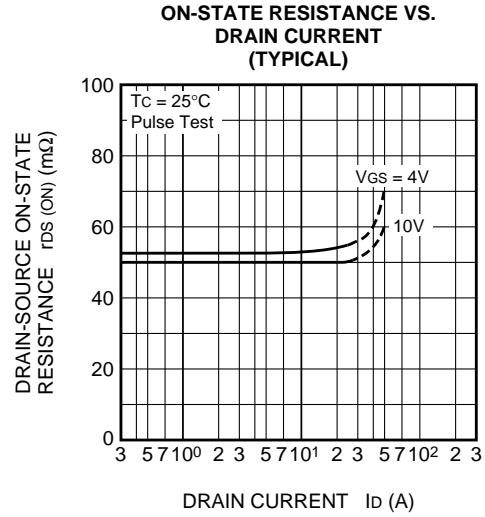
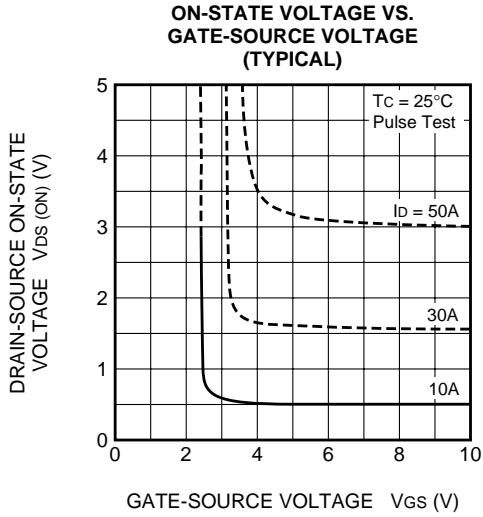


OUTPUT CHARACTERISTICS (TYPICAL)



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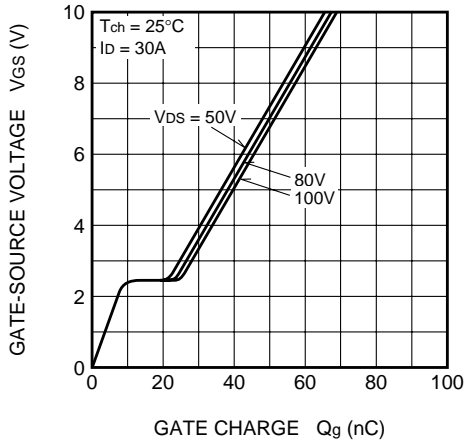
HIGH-SPEED SWITCHING USE



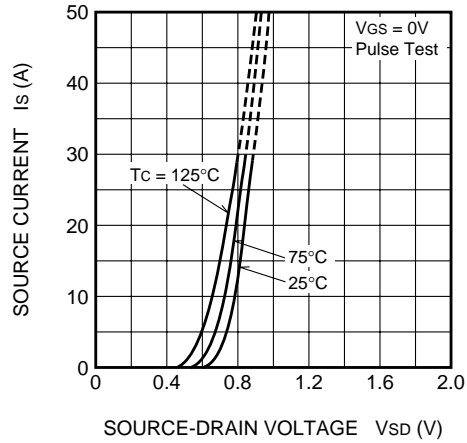
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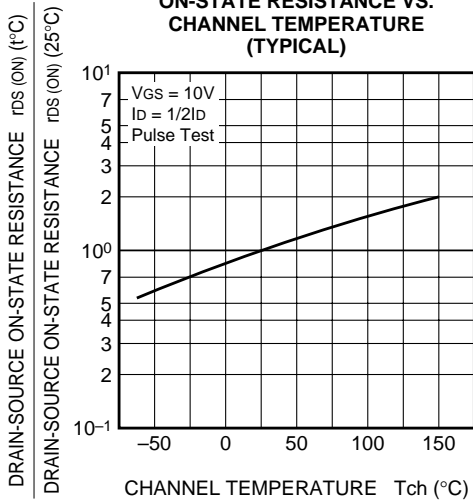
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



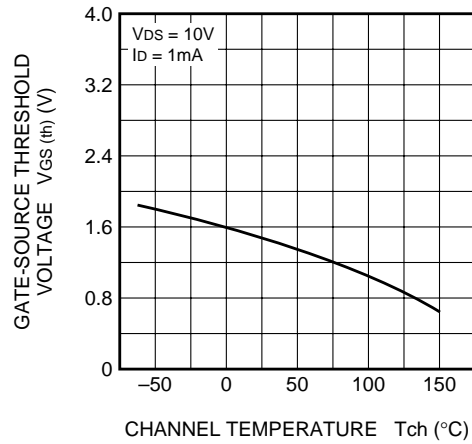
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



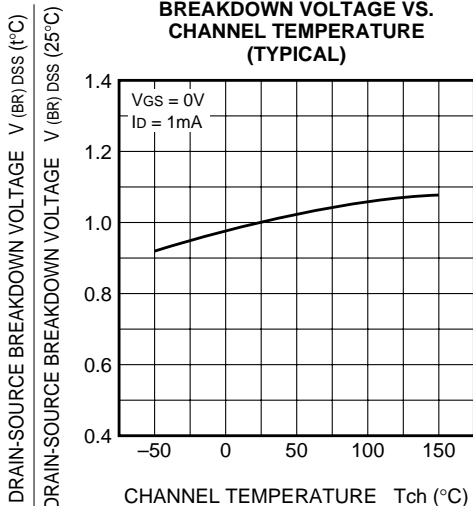
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

